Photocouplers Infrared LED & Photo Transistor

TLP383

1. Applications

- Programmable Logic Controllers (PLCs)
- AC Adapters
- I/O Interface Boards

2. General

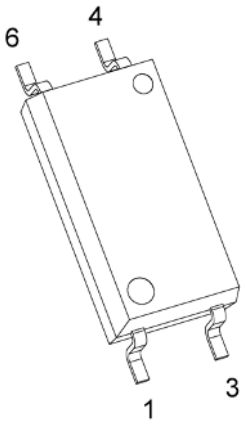
TLP383 is a photocoupler of low input and high isolation type that consists of phototransistor optically coupled to infrared LED in a 4-pin SO6L package. TLP383 is guaranteed high isolation voltage (5000 Vrms) and wide operating temperature (T_a = -55 to 125 ℃). Since TLP383 has a small and thin package compared with a standard DIP package, it is suitable for high-density surface mounting applications such as programmable controllers.

3. Features

(1) Collector-emitter voltage: 80 V (min)
(2) Current transfer ratio: 50 % (min)
GB Rank: 100 % (min)
(3) Isolation voltage: 5000 Vrms (min)
(4) Operating temperature: -55 to 125 ℃
(5) Safety standards
UL-recognized: UL 1577, File No.E67349
cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349
VDE-approved: EN 60747-5-5, EN 62368-1 **(Note 1)**
CQC-approved: GB4943.1, GB8898 Thailand Factory

Note 1: When a VDE approved type is needed, please designate the **Option (D4)**.

4. Packaging and Pin Assignment



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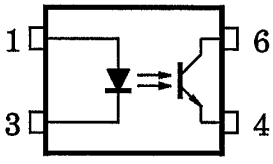

1: Anode
3: Cathode
4: Emitter
6: Collector

Start of commercial production
2015-01

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5. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	8.0	mm
Clearance	8.0	
Internal isolation thickness	0.4	

6. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

	Characteristics		Symbol	Note	Rating	Unit
LED	Input forward current		I_F		50	mA
	Input forward current derating	($T_a \geq 90$ °C)	$\Delta I_F/\Delta T_a$		-1.11	mA/°C
	Input forward current (pulsed)		I_{FP}	(Note 1)	1	A
	Input power dissipation		P_D		100	mW
	Input power dissipation derating	($T_a \geq 90$ °C)	$\Delta P_D/\Delta T_a$		-2.22	mW/°C
	Input reverse voltage		V_R		5	V
	Junction temperature		T_j		135	°C
Detector	Collector-emitter voltage		V_{CEO}		80	V
	Emitter-collector voltage		V_{ECO}		7	V
	Collector current		I_C		50	mA
	Collector power dissipation		P_C		150	mW
	Collector power dissipation derating	($T_a \geq 25$ °C)	$\Delta P_C/\Delta T_a$		-1.36	mW/°C
	Junction temperature		T_j		135	°C
Common	Operating temperature		T_{opr}		-55 to 125	°C
	Storage temperature		T_{stg}		-55 to 125	°C
	Lead soldering temperature	(10 s)	T_{sol}		260	°C
	Total power dissipation		P_T		250	mW
	Total power dissipation derating	($T_a \geq 25$ °C)	$\Delta P_T/\Delta T_a$		-2.27	mW/°C
	Isolation voltage	(AC, 60 s, R.H. ≤ 60 %)	BV_S	(Note 2)	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) ≤ 0.1 ms, f = 100 Hz

Note 2: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4 and 6 are shorted together.

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7. Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

	Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
LED	Input forward voltage	V_F		I_F = 10 mA	1.1	1.25	1.4	V
	Input reverse current	I_R		V_R = 5 V	—	—	5	μA
	Input capacitance	C_t		V = 0 V, f = 1 MHz	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$		I_C = 0.5 mA	80	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$		I_E = 0.1 mA	7	—	—	V
	Dark Current	I_{DARK}		V_{CE} = 48 V	—	0.01	0.08	μA
				V_{CE} = 48 V, T_a = 85 °C	—	2	50	
	Collector-emitter capacitance	C_{CE}		V = 0 V, f = 1 MHz	—	10	—	pF

8. Coupled Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	I_C/I_F	(Note 1)	I_F = 5 mA, V_{CE} = 5 V	50	—	600	%
			I_F = 5 mA, V_{CE} = 5 V, GB Rank	100	—	600	
			I_F = 0.5 mA, V_{CE} = 5 V	50	—	600	
			I_F = 0.5 mA, V_{CE} = 5 V, GB Rank	100	—	600	
Saturated current transfer ratio	$I_C/I_{F(sat)}$		I_F = 1 mA, V_{CE} = 0.4 V	—	60	—	%
			I_F = 1 mA, V_{CE} = 0.4 V, GB Rank	30	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$		I_F = 8 mA, I_C = 2.4 mA	—	—	0.3	V
			I_F = 1 mA, I_C = 0.2 mA	—	0.09	—	
			I_F = 1 mA, I_C = 0.2 mA, GB Rank	—	—	0.3	
OFF-state collector current	$I_{C(off)}$		V_{CE} = 48 V, V_F = 0.7 V	—	—	10	μA

Note 1: See Table 8.1 for current transfer ratio.

Table 8.1 Current Transfer Ratio (CTR) Rank (Note) (Unless otherwise specified, T_a = 25 °C)

Rank	Rank short code	Note	Test Condition	Current transfer ratio I_C/I_F Min	Current transfer ratio I_C/I_F Max	Marking of classification	Unit
Blank	—		I_F = 5 mA, V_{CE} = 5 V	50	600	Blank, YE, GR, GB, Y+, G, G+, BL, B	%
			I_F = 0.5 mA, V_{CE} = 5 V				
Y	—		I_F = 5 mA, V_{CE} = 5 V	50	150	YE	
			I_F = 0.5 mA, V_{CE} = 5 V				
GR	—		I_F = 5 mA, V_{CE} = 5 V	100	300	GR	
			I_F = 0.5 mA, V_{CE} = 5 V				
GB	—		I_F = 5 mA, V_{CE} = 5 V	100	600	GB, GR, BL	
			I_F = 0.5 mA, V_{CE} = 5 V				
BL	—		I_F = 5 mA, V_{CE} = 5 V	200	600	BL	
			I_F = 0.5 mA, V_{CE} = 5 V				
YH	—		I_F = 0.5 mA, V_{CE} = 5 V	75	150	Y+	
GRL	GL	(Note 1)	I_F = 0.5 mA, V_{CE} = 5 V	100	200	G	
GRH	GH	(Note 1)	I_F = 0.5 mA, V_{CE} = 5 V	150	300	G+	
BLL	B	(Note 1)	I_F = 0.5 mA, V_{CE} = 5 V	200	400	B	

Note: Specify both the part number and a rank in this format when ordering.
Example: TLP383(GB,E
For safety standard certification, however, specify the part number alone.
Example: TLP383(GB,E: TLP383

Note 1: A rank in the order name is sometimes omitted like above "Rank short code".

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9. Isolation Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	(Note 1)	V_S = 0 V, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	(Note 1)	V_S = 500 V, RH ≤ 60 %	10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	(Note 1)	AC, 60 s	5000	—	—	Vrms

Note 1: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4 and 6 are shorted together.

10. Switching Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Rise time	t_r		V_{CC} = 10 V, I_C = 2 mA, R_L = 100 Ω	—	2	—	μs
Fall time	t_f			—	3	—	
Turn-on time	t_{on}			—	3	—	
Turn-off time	t_{off}			—	3	—	
Turn-on time	t_{on}		See Fig. 10.1. R_L = 1.9 kΩ, V_{CC} = 5 V, I_F = 16 mA	—	0.95	—	
Storage time	t_s			—	14	—	
Turn-off time	t_{off}			—	28	—	
Turn-on time	t_{on}		See Fig. 10.1. R_L = 4.7 kΩ, V_{CC} = 5 V, I_F = 1.6 mA	—	7.5	—	
Storage time	t_s			—	7	—	
Turn-off time	t_{off}			—	30	—	

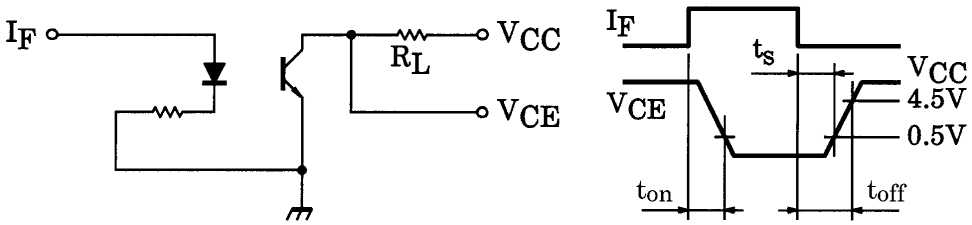

Fig. 10.1 Switching Time Test Circuit and Waveform

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11. Characteristics Curves (Note)

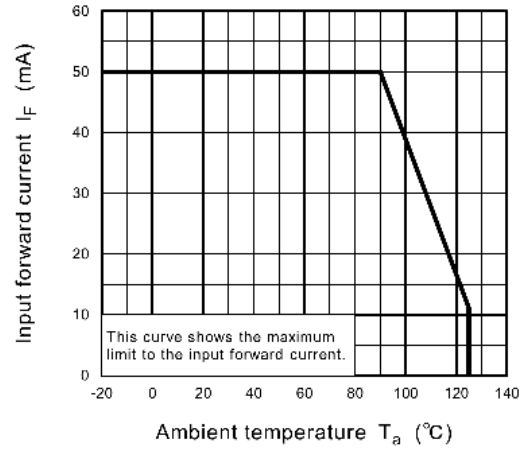

Fig. 11.1 I_F - T_a

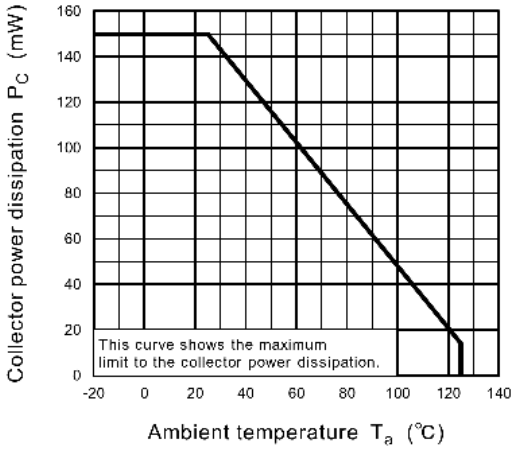

Fig. 11.2 P_C - T_a

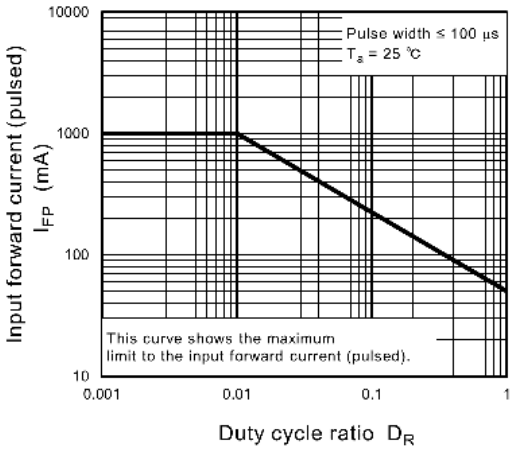

Fig. 11.3 I_{FP} - D_R

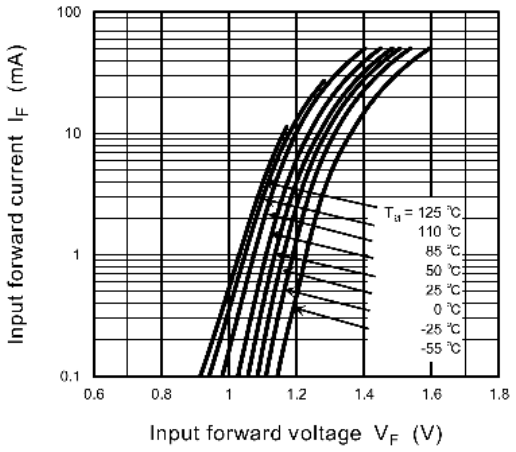

Fig. 11.4 I_F - V_F

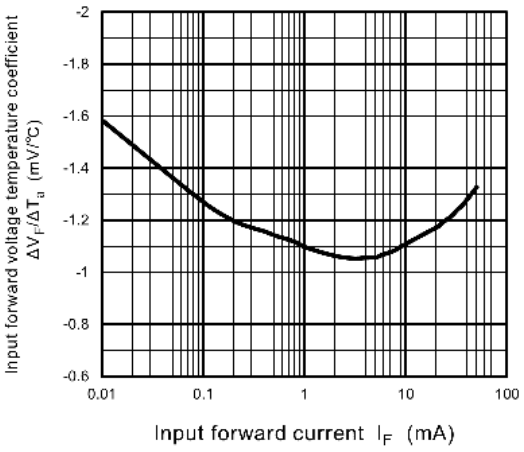

Fig. 11.5 $\Delta V_F/\Delta T_a$ - I_F

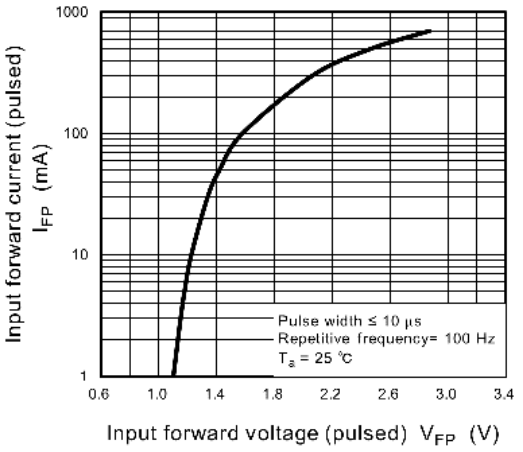

Fig. 11.6 I_{FP} - V_{FP}

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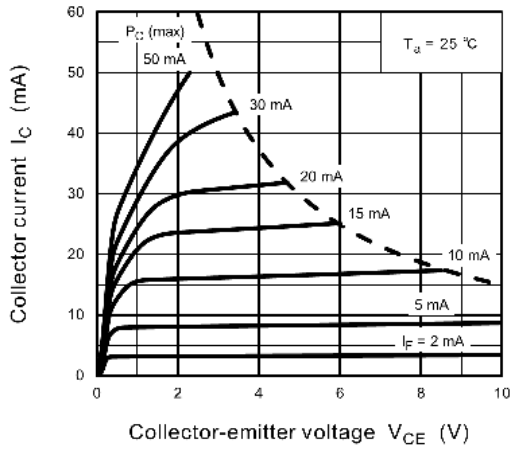

Fig. 11.7 I_C - V_{CE}

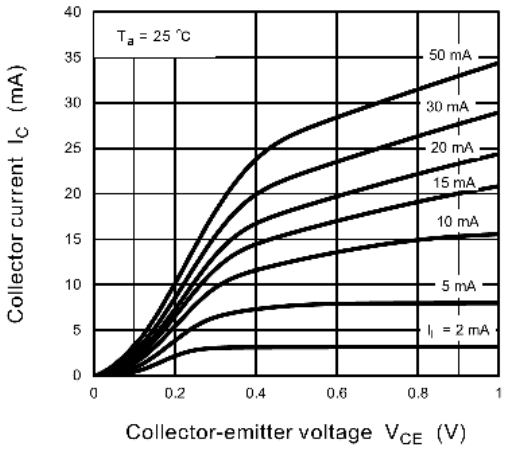

Fig. 11.8 I_C - V_{CE}

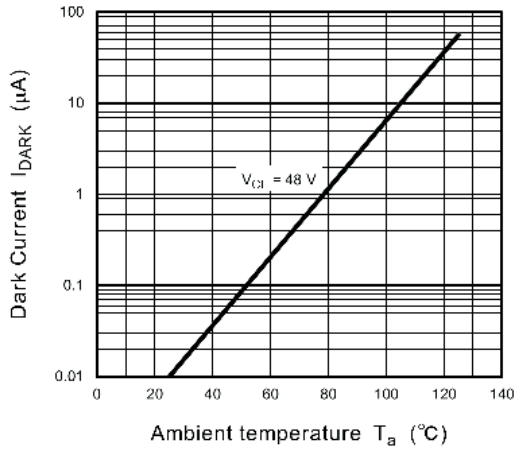

Fig. 11.9 I_{DARK} - T_a

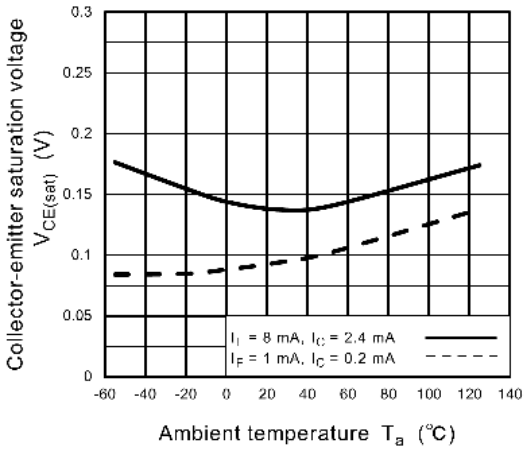

Fig. 11.10 $V_{CE(sat)}$ - T_a

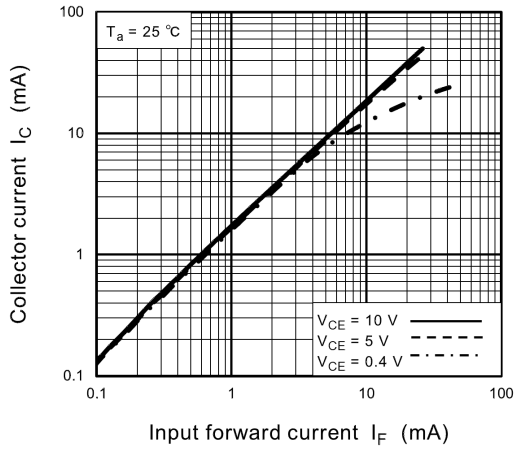

Fig. 11.11 I_C - I_F

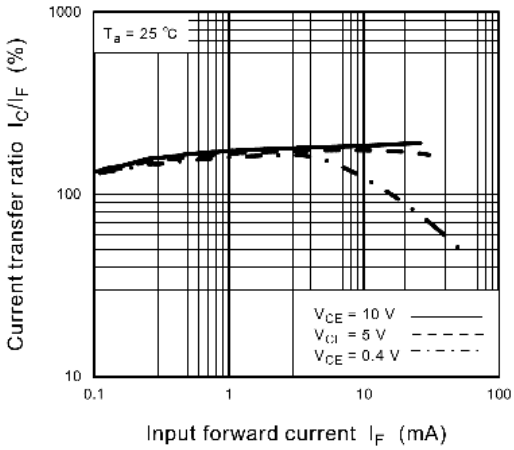

Fig. 11.12 I_C/I_F - I_F

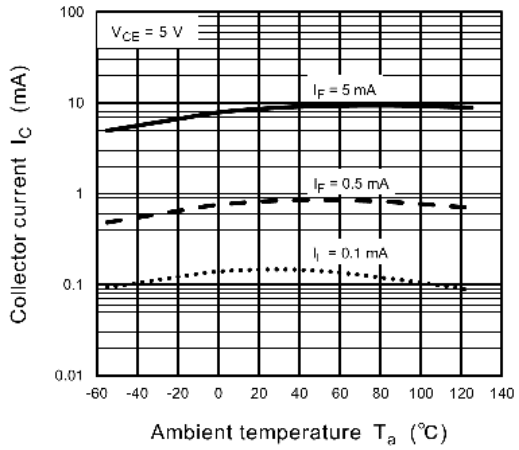

Fig. 11.13 I_C - T_a

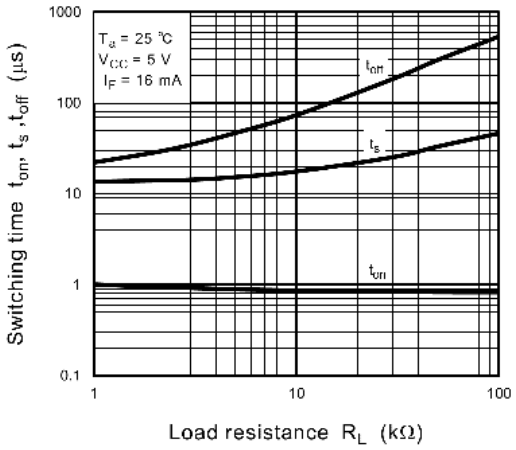

Fig. 11.14 Switching Time - R_L

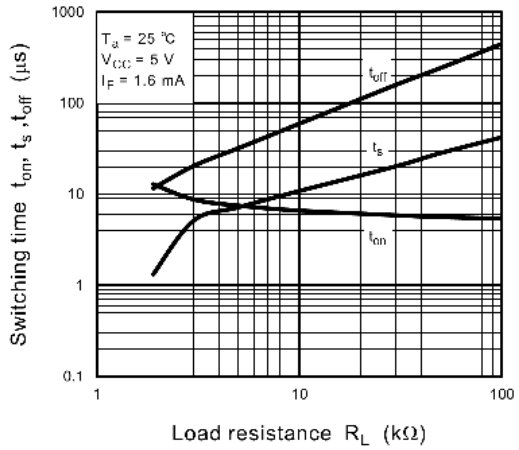

Fig. 11.15 Switching Time - R_L

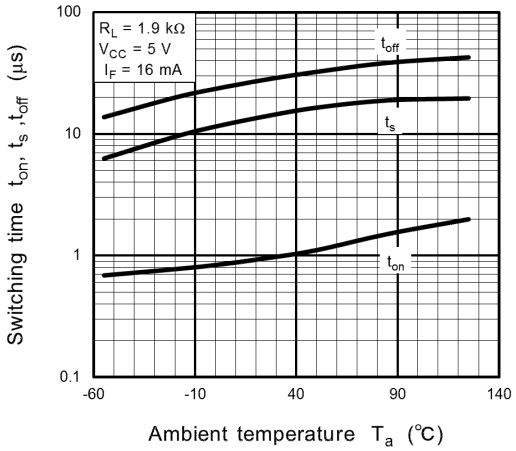

Fig. 11.16 Switching Time - T_a

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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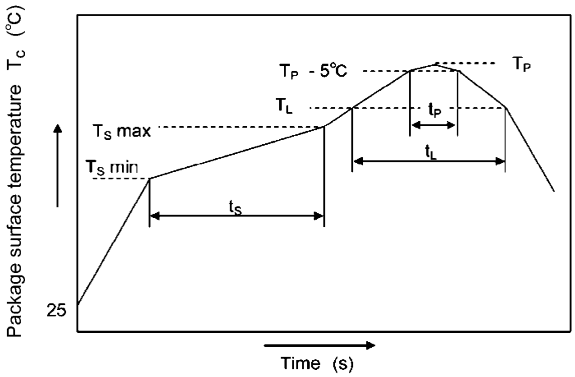
12. Soldering and Storage

12.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

- When using soldering reflow.
  The soldering temperature profile is based on the package surface temperature.
  (See the figure shown below, which is based on the package surface temperature.)
  Reflow soldering must be performed once or twice.
  The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	T_S	150	200	°C
Preheat time	t_S	60	120	s
Ramp-up rate (T_L to T_P)			3	°C/s
Liquidus temperature	T_L	217		°C
Time above T_L	t_L	60	150	s
Peak temperature	T_P		260	°C
Time during which T_c is between (T_P – 5) and T_P	t_P		30	s
Ramp-down rate (T_P to T_L)			6	°C/s

Fig. 12.1.1 An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

- When using soldering flow
  Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
  Mounting condition of 260 °C within 10 seconds is recommended.
  Flow soldering must be performed once.
- When using soldering Iron
  Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C
  Heating by soldering iron must be done only once per lead.

12.2. Precautions for General Storage

- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

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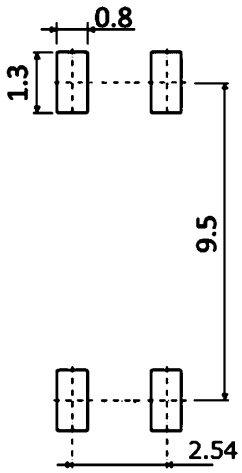
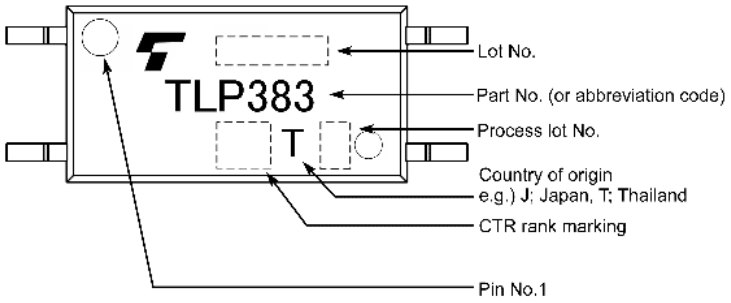
13. Land Pattern Dimensions (for reference only)



Unit: mm

14. Marking (Note)



Note: For the CTR rank mark, please refer to the marking of classification in table 8.1 CTR rank table.

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15. EN 60747-5-5 Option (D4) Specification

- Part number: TLP383 **(Note 1)**
- The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN 60747.

  Example: TLP383(D4GR-TL,E

  D4: EN 60747 option
  GR: CTR rank
  TL: Tape type (TPL)
  E: [[G]]/RoHS COMPATIBLE **(Note 2)**

Note 1: Use TOSHIBA standard type number for safety standard application.
e.g., TLP383(D4GR-TL,E → TLP383

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.
RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description	Symbol	Rating	Unit
Application classification for rated mains voltage ≤ 600 Vrms for rated mains voltage ≤ 1000 Vrms		 I-IV I-III	—
Climatic classification		55 / 125 / 21	—
Pollution degree		2	—
Maximum operating insulation voltage	V_{IORM}	1500	Vpeak
Input to output test voltage, Method A V_{pr} = 1.6 × V_{IORM}, type and sample test t_p = 10 s, partial discharge < 5 pC	V_{pr}	2400	Vpeak
Input to output test voltage, Method B V_{pr} =1.875 × V_{IORM}, 100 % production test t_p = 1 s, partial discharge < 5 pC	V_{pr}	2813	Vpeak
Highest permissible overvoltage (transient overvoltage, t_{pr} = 60 s)	V_{TR}	8000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve) current (input current I_F, P_{SO} = 0) power (output or total power dissipation) temperature	 I_{si} P_{SO} T_S	 250 400 150	 mA mW °C
Insulation resistance V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_S	R_{si}	≥ 10^{12} ≥ 10^{11} ≥ 10^{9}	Ω

Fig. 15.1 EN 60747 Insulation Characteristics

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Minimum creepage distance	Cr	8.0 mm
Minimum clearance	Cl	8.0 mm
Minimum insulation thickness	ti	0.4 mm
Comparative tracking index	CTI	500

Fig. 15.2 Insulation Related Specifications (Note)

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.

Fig. 15.3 Marking on packing

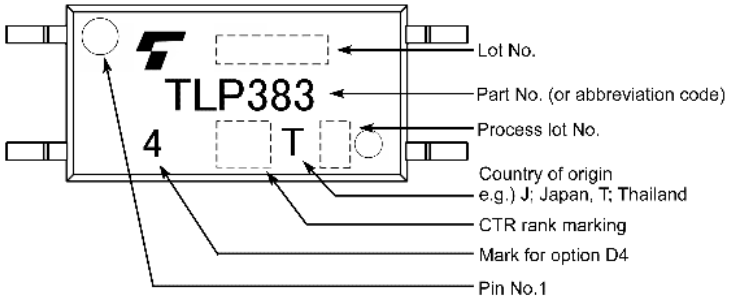


Fig. 15.4 Marking Example (Note)

Note: The above marking is applied to the photocouplers that have been qualified according to option (D4) of EN 60747.

Figure 1 Partial discharge measurement procedure according to EN 60747
Destructive test for qualification and sampling tests.

Method A

(for type and sampling tests, destructive tests)

t_1, t_2	= 1 to 10 s
t_3, t_4	= 1 s
t_p (Measuring time for partial discharge)	= 10 s
t_b	= 12 s
t_{ini}	= 60 s

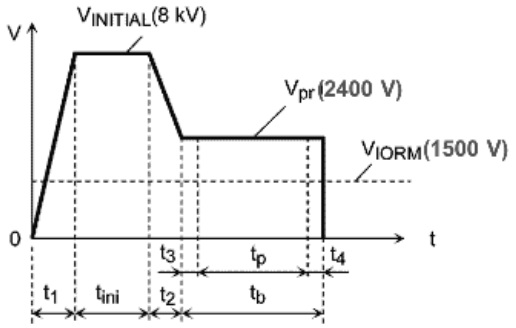


Figure 2 Partial discharge measurement procedure according to EN 60747
Non-destructive test for 100 % inspection.

Method B

(for sample test,non-destructive test)

t_3, t_4	= 0.1 s
t_p (Measuring time for partial discharge)	= 1 s
t_b	= 1.2 s

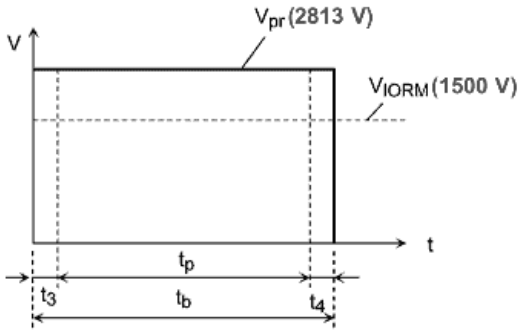


Figure 3 Dependency of maximum safety ratings on ambient temperature

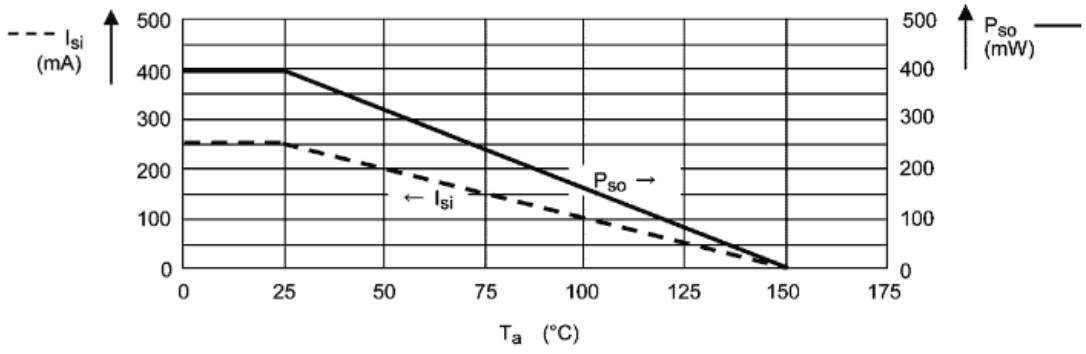
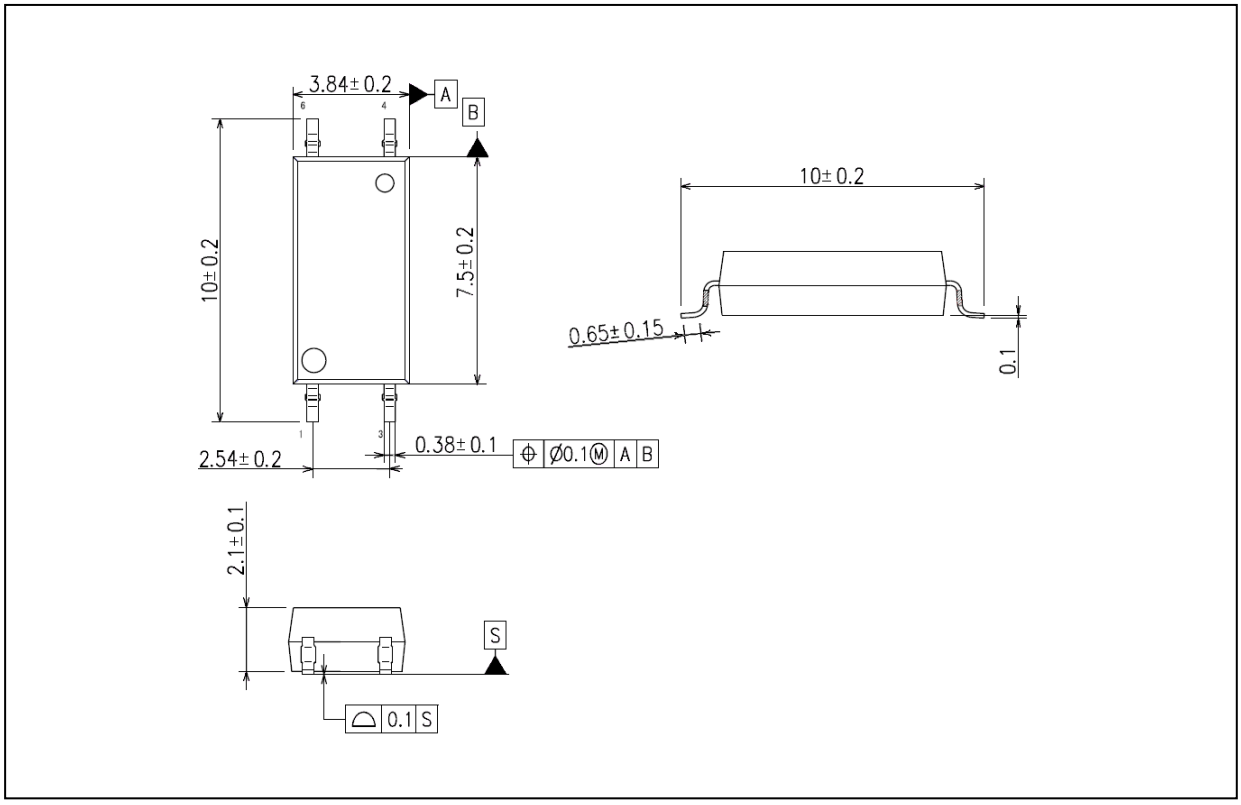


Fig. 15.5 Measurement Procedure

Package Dimensions

Unit: mm



Weight: 0.128 g (typ.)

Package Name(s)
TOSHIBA: 11-4P1A

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